

F DN5618P

60V P-Channel Logic Level PowerTrench® MOSFET

General Description

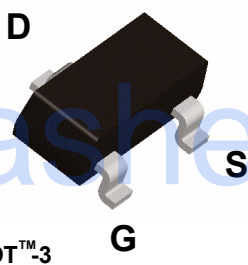
This 60V P-Channel MOSFET uses Fairchild's high voltage PowerTrench process. It has been optimized for power management applications.

Applications

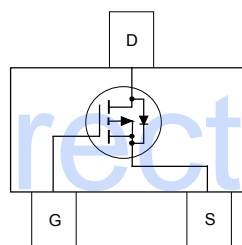
- DC-DC converters
- Load switch
- Power management

Features

- -1.25 A, -60 V. $R_{DS(ON)} = 0.170 \Omega @ V_{GS} = -10 V$
 $R_{DS(ON)} = 0.230 \Omega @ V_{GS} = -4.5 V$
- Fast switching speed
- High performance trench technology for extremely low $R_{DS(ON)}$



SuperSOT™-3



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{DSS}	Drain-Source Voltage	-60	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current – Continuous (Note 1a)	-1.25	A
	– Pulsed	-10	
P _D	Maximum Power Dissipation (Note 1a) (Note 1b)	0.5	W
		0.46	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)	250	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case (Note 1)	75	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
618	F DN5618P	7"	8mm	3000 units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-60			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		-58		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -48\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
I_{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-1	-1.6	-3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		4		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = -10\text{ V}, I_D = -1.25\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -1.0\text{ A}$ $V_{GS} = -10\text{ V}, I_D = -3\text{ A}, T_J = 125^\circ\text{C}$		0.148 0.185 0.245	0.170 0.230 0.315	Ω
$I_{D(on)}$	On–State Drain Current	$V_{GS} = -10\text{ V}, V_{DS} = -5\text{ V}$	-5			A
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{ V}, I_D = -1.25\text{ A}$		4.3		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$		430		pF
C_{oss}	Output Capacitance	$f = 1.0\text{ MHz}$		52		pF
C_{rss}	Reverse Transfer Capacitance			19		pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -30\text{ V}, I_D = -1\text{ A}$		6.5	13	ns
t_r	Turn–On Rise Time	$V_{GS} = -10\text{ V}, R_{GEN} = 6\ \Omega$		8	16	ns
$t_{d(off)}$	Turn–Off Delay Time			16.5	30	ns
t_f	Turn–Off Fall Time			4	8	ns
Q_g	Total Gate Charge	$V_{DS} = -30\text{ V}, I_D = -1.25\text{ A}$		8.6	13.8	nC
Q_{gs}	Gate–Source Charge	$V_{GS} = -10\text{ V}$		1.5		nC
Q_{gd}	Gate–Drain Charge			1.3		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				-0.42	A
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -0.42$ (Note 2)		-0.7	-1.2	V

Notes:

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 250°C/W when mounted on a 0.02 in^2 pad of 2 oz. copper.



b) 270°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle ≤ 2.0

Typical Characteristics

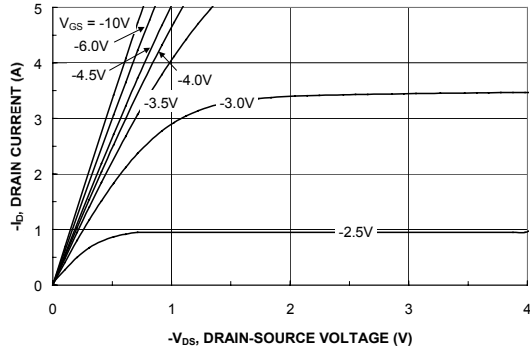


Figure 1. On-Region Characteristics.

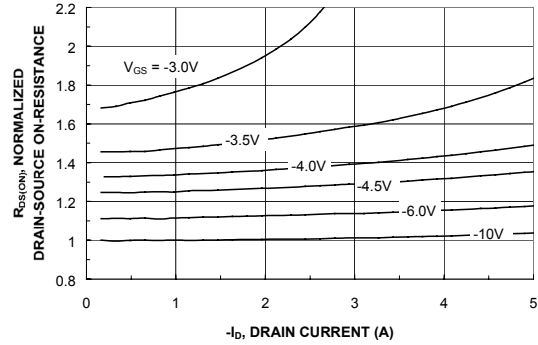


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

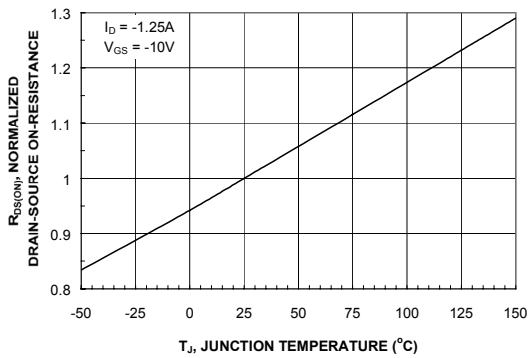


Figure 3. On-Resistance Variation with Temperature.

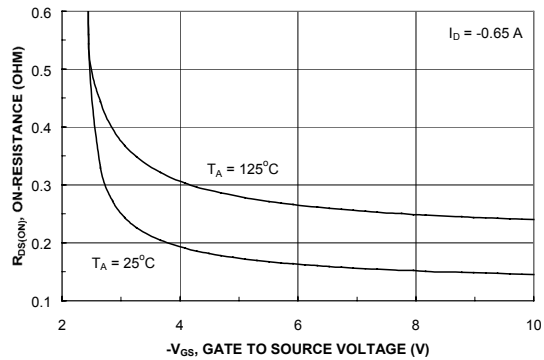


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

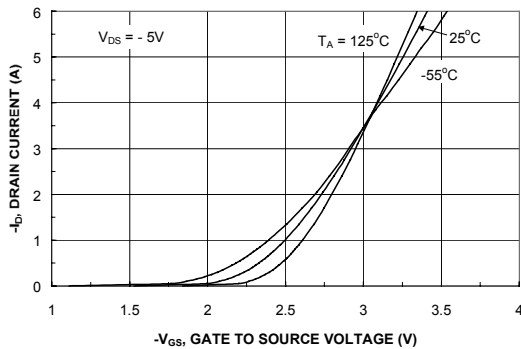


Figure 5. Transfer Characteristics.

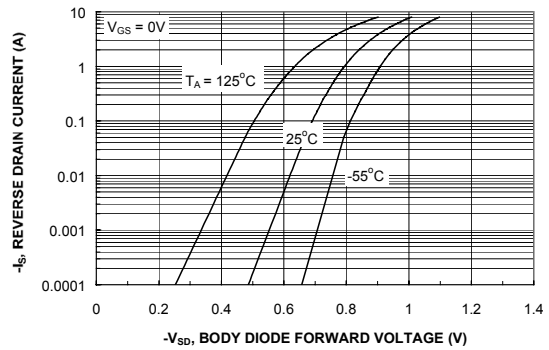


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

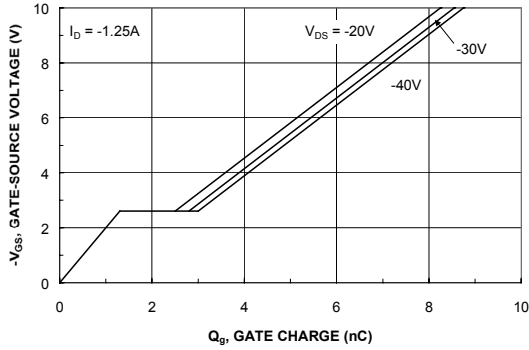


Figure 7. Gate Charge Characteristics.

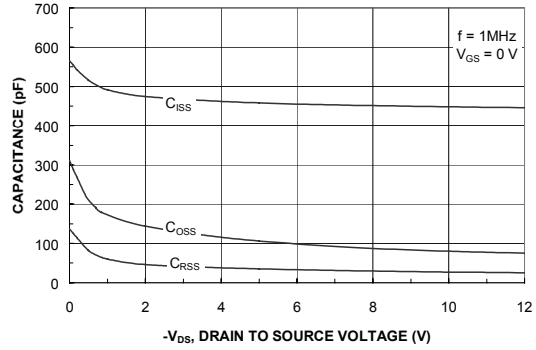


Figure 8. Capacitance Characteristics.

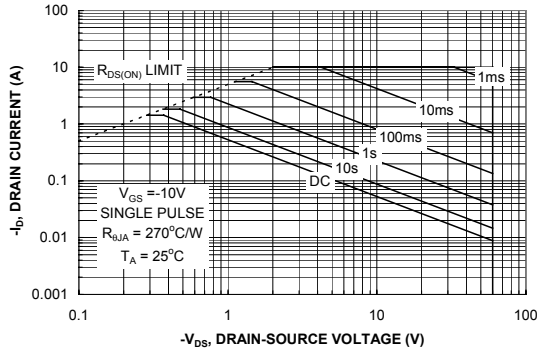


Figure 9. Maximum Safe Operating Area.

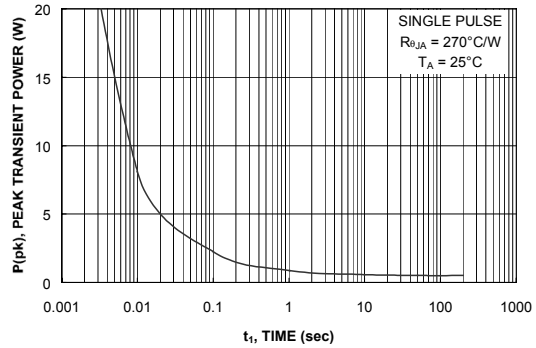


Figure 10. Single Pulse Maximum Power Dissipation.

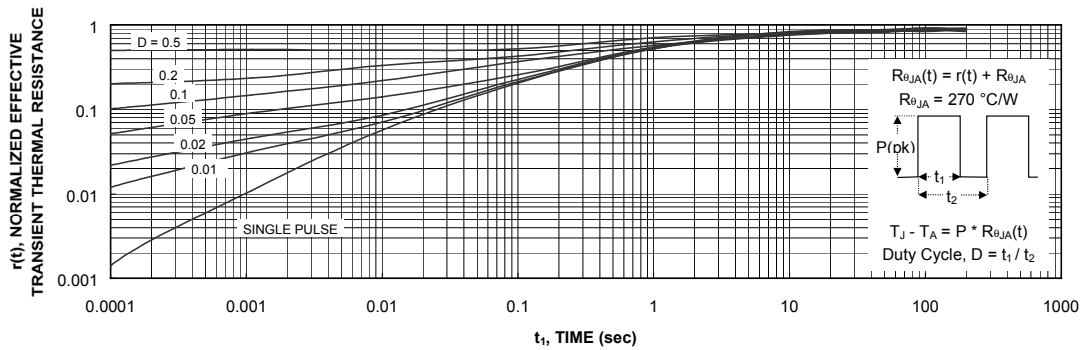


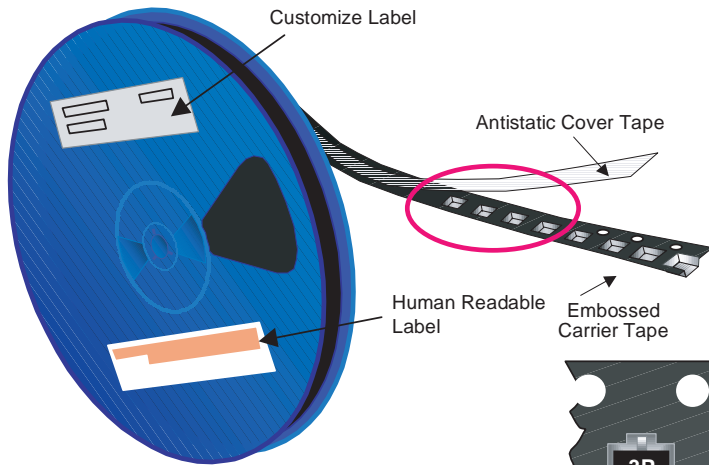
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

SuperSOT™-3 Tape and Reel Data



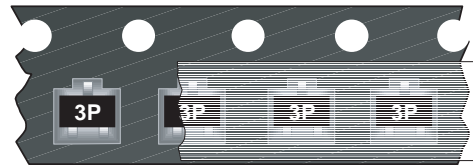
SSOT-3 Packaging Configuration: Figure 1.0



Packaging Description:

SSOT-3 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 177cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 10,000 units per 13" or 330cm diameter reel. This and some other options are described in the Packaging Information table.

These full reels are individually labeled and placed inside a standard intermediate made of recyclable corrugated brown paper with a Fairchild logo printing. One pizza box contains eight reels maximum. And these intermediate boxes are placed inside a labeled shipping box which comes in different sizes depending on the number of parts shipped.

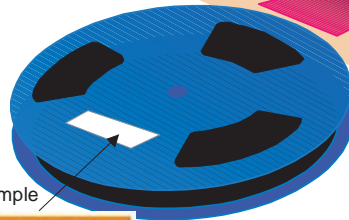


SSOT-3 Std Unit Orientation

SSOT-3 Std Packaging Information		
Packaging Option	Standard (no flow code)	D87Z
Packaging type	TNR	TNR
Qty per Reel/Tube/Bag	3,000	10,000
Reel Size	7" Dia	13"
Box Dimension (mm)	187x107x183	343x343x64
Max qty per Box	24,000	30,000
Weight per unit (gm)	0.0097	0.0097
Weight per Reel (kg)	0.1230	0.4150
Note/Comments		

343mm x 342mm x 64mm Intermediate box for D87Z Option

Human Readable Label



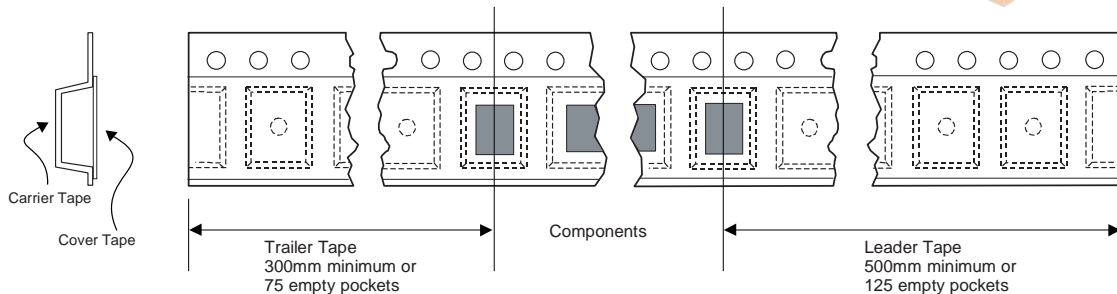
Human Readable Label sample



Human Readable Label

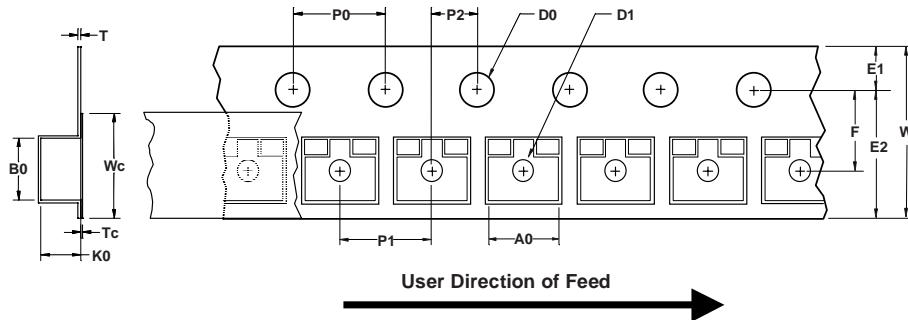
187mm x 107mm x 183mm Intermediate Box for Standard Option

SSOT-3 Tape Leader and Trailer Configuration: Figure 2.0



SuperSOT™-3 Tape and Reel Data, continued

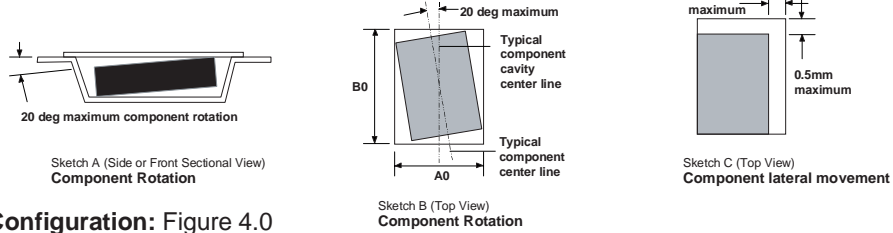
SSOT-3 Embossed Carrier Tape Configuration: Figure 3.0



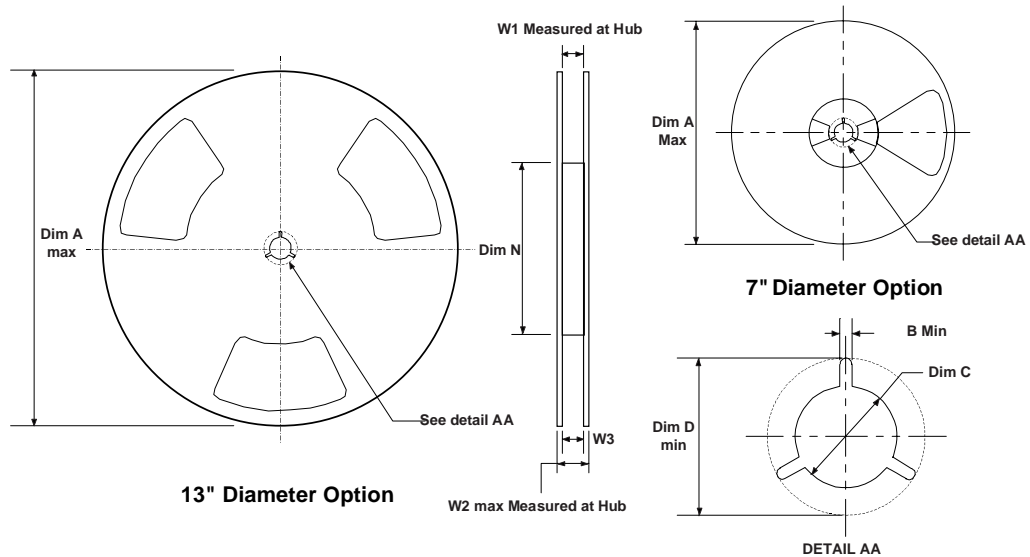
Dimensions are in millimeter

Pkg type	A0	B0	W	D0	D1	E1	E2	F	P1	P0	K0	T	Wc	Tc
SSOT-3 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



SSOT-3 Reel Configuration: Figure 4.0

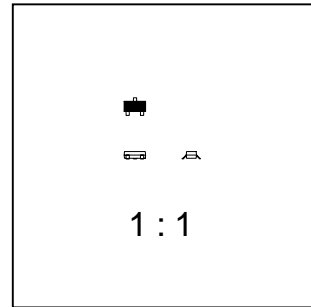
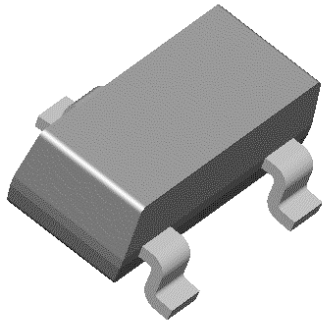


Dimensions are in inches and millimeters

Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SuperSOT™-3 Package Dimensions

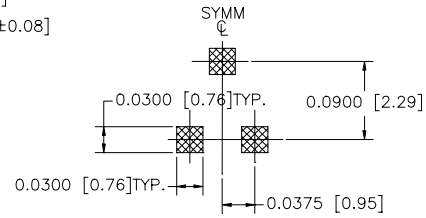
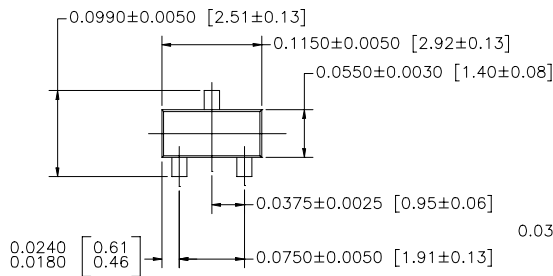
SuperSOT™-3 (FS PKG Code 32)



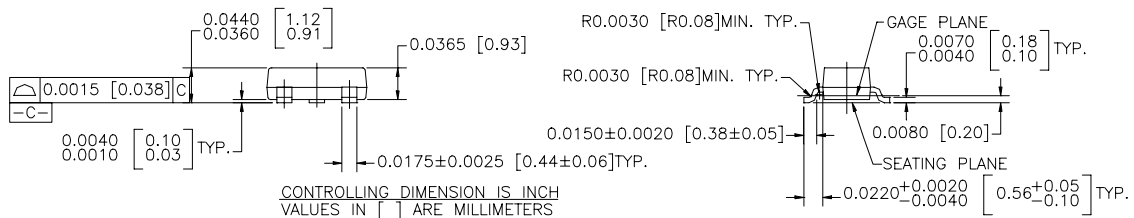
Scale 1:1 on letter size paper

Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0097



LAND PATTERN RECOMMENDATION



NOTES : UNLESS OTHERWISE SPECIFIED

SUPER SOT , 3 LEADS

- STANDARD LEAD FINISH TO BE 150 MICRONS / 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
- NO JEDEC REGISTRATION AS OF DEC. 1995.

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DOME TM	ISOPANAR TM	SuperSOT TM -3	
E ² CMOS TM	MICROWIRE TM	SuperSOT TM -6	
EnSigna TM	OPTOLOGIC TM	SuperSOT TM -8	
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PRODUCT STATUS DEFINITIONS

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